

September 13, 2011

## Product Specifications of the NESG7030M04, SiGe:C HBT

- The device is an ideal choice for low noise, high-gain amplification  
NF = 0.75 dB TYP., Ga = 14.0 dB TYP., @V<sub>CE</sub> = 2 V, I<sub>c</sub> = 7 mA, f = 5.8 GHz
- Collector to Base breakdown voltage is 4.3 V and more
- Flat-lead 4-pin thin-type super minimold package
- Pb-free product